

ZXTN25100BFH

100V, SOT23, medium power transistor

Summary

$BV_{CEX} > 170V$

$BV_{CEO} > 100V$

$BV_{ECO} > 6V$

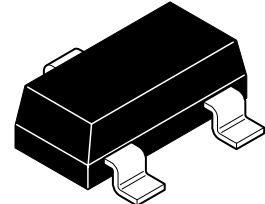
$I_{C(cont)} = 3A$

$V_{CE(sat)} < 80mV @ 1A$

$R_{CE(sat)} = 67m\Omega$

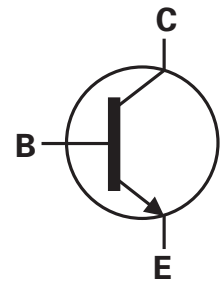
$P_D = 1.25W$

Complementary part number ZXTP25100BFH



Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

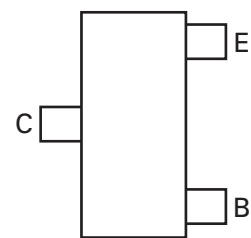


Features

- High power dissipation SOT23 package
- Low saturation voltage
- 170V forward blocking voltage

Applications

- Lamp relay and solenoid drivers
- General switching in automotive and industrial applications
- Motor drive and control



Pinout - top view

Ordering information

| Device | Reel size (inches) | Tape width (mm) | Quantity per reel |
|----------------|--------------------|-----------------|-------------------|
| ZXTN25100BFHTA | 7 | 8 | 3,000 |

Device marking

021

ZXTN25100BFH

Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
|--|----------------|-------------|-------|
| Collector-base voltage | V_{CBO} | 170 | V |
| Collector-emitter voltage (forward blocking) | V_{CEX} | 170 | V |
| Collector-emitter voltage | V_{CEO} | 100 | V |
| Emitter-collector voltage (reverse blocking) | V_{ECO} | 6 | V |
| Emitter-base voltage | V_{EBO} | 7 | V |
| Continuous collector current ^(b) | I_C | 3 | A |
| Peak pulse current | I_{CM} | 9 | A |
| Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$ | P_D | 0.73 | W |
| Linear derating factor | | 5.84 | mW/°C |
| Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$ | P_D | 1.05 | W |
| Linear derating factor | | 8.4 | mW/°C |
| Power dissipation at $T_{amb} = 25^{\circ}C^{(c)}$ | P_D | 1.25 | W |
| Linear derating factor | | 9.6 | mW/°C |
| Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$ | P_D | 1.81 | W |
| Linear derating factor | | 14.5 | mW/°C |
| Operating and storage temperature range | T_j, T_{stg} | - 55 to 150 | °C |

Thermal resistance

| Parameter | Symbol | Limit | Unit |
|------------------------------------|-----------------|-------|------|
| Junction to ambient ^(a) | $R_{\theta JA}$ | 171 | °C/W |
| Junction to ambient ^(b) | $R_{\theta JA}$ | 119 | °C/W |
| Junction to ambient ^(c) | $R_{\theta JA}$ | 100 | °C/W |
| Junction to ambient ^(d) | $R_{\theta JA}$ | 69 | °C/W |

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

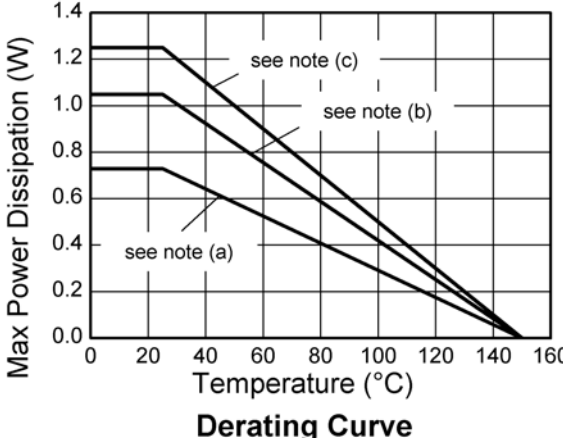
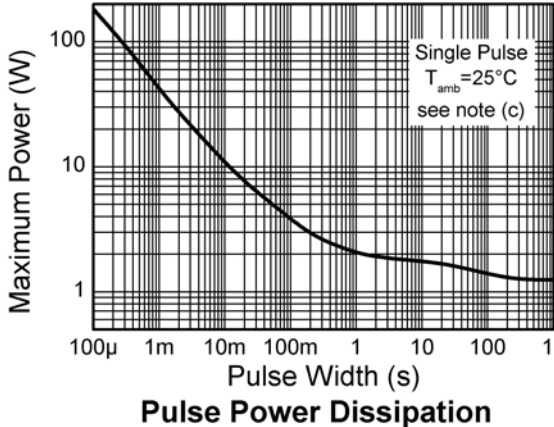
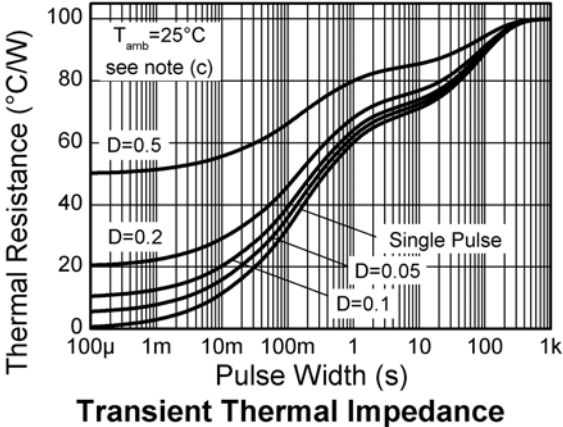
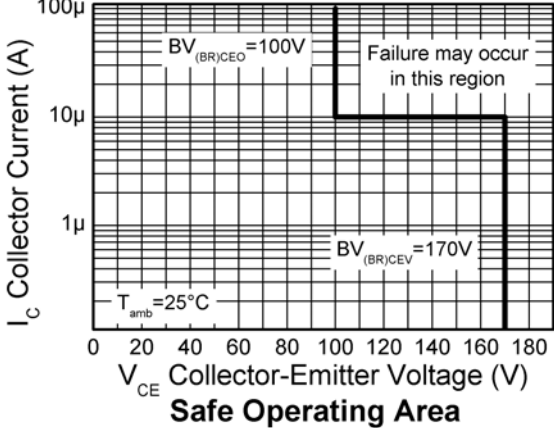
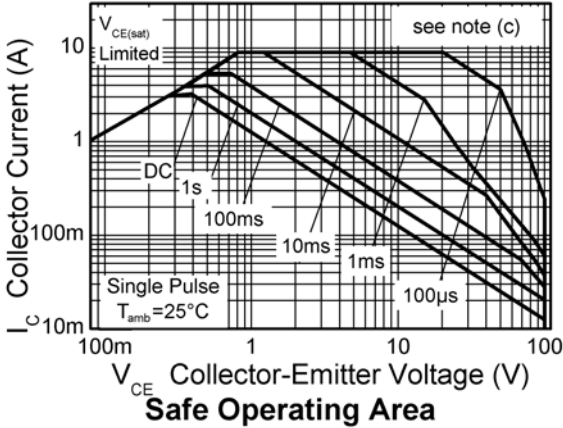
(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at $t < 5$ secs.

ZXTN25100BFH

Characteristics



ZXTN25100BFH

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

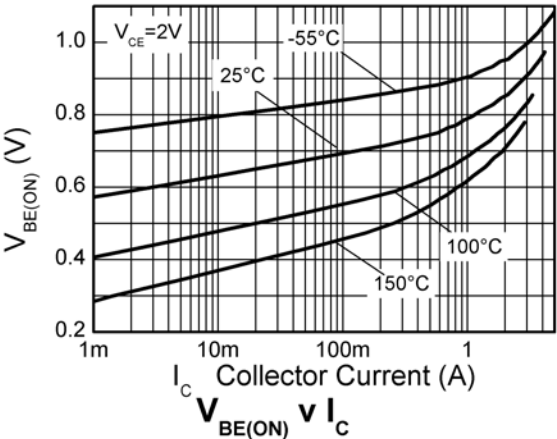
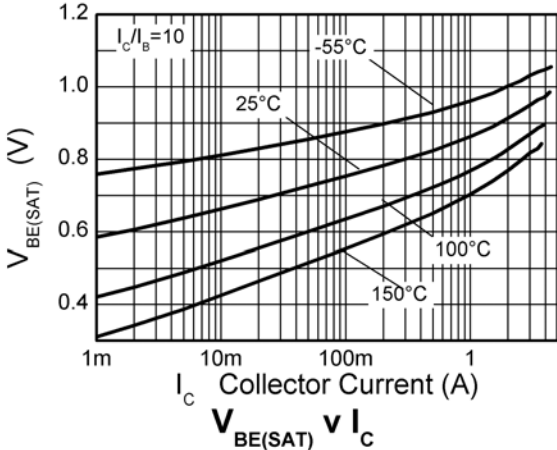
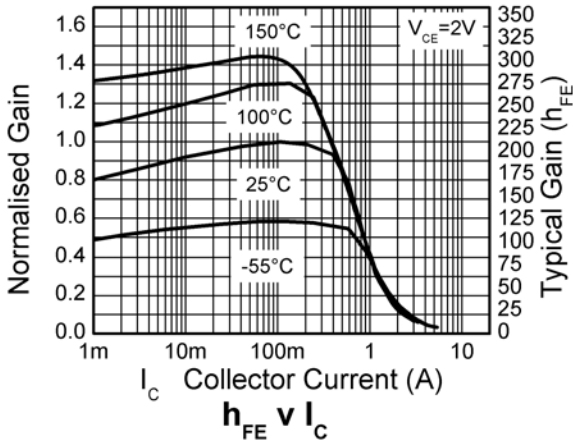
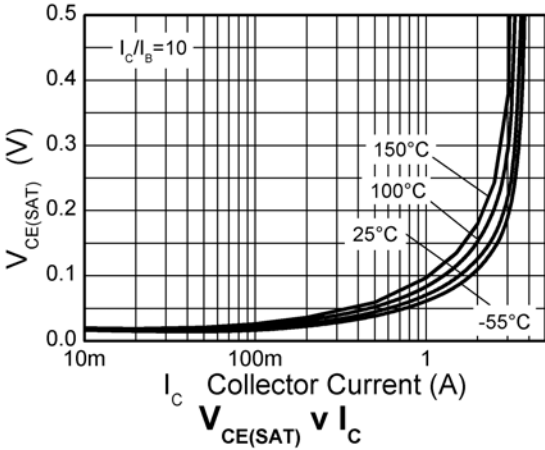
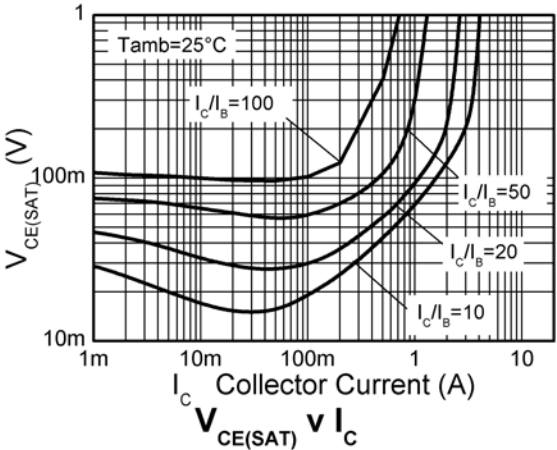
| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--|---------------|-----------|------------------------|------------------------|----------------------|--|
| Collector-base breakdown voltage | BV_{CBO} | 170 | 220 | | V | $I_C = 100\mu\text{A}$ |
| Collector-emitter breakdown voltage (forward blocking) | BV_{CEX} | 170 | 210 | | | $I_C = 100\mu\text{A}$, $R_{BE} < 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$ |
| Collector-emitter breakdown voltage (base open) | BV_{CEO} | 100 | 120 | | V | $I_C = 10\text{mA}^{(*)}$ |
| Emitter-collector breakdown voltage (reverse blocking) | BV_{ECX} | 6 | 7 | | V | $I_E = 100\mu\text{A}$, $R_{BC} < 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$ |
| Emitter-collector breakdown voltage (base open) | BV_{ECO} | 6 | 8.4 | | V | $I_E = 100\mu\text{A}$, |
| Emitter-base breakdown voltage | BV_{EBO} | 7 | 8 | | V | $I_E = 100\mu\text{A}$ |
| Collector cut-off current | I_{CBO} | | <1 | 50 20 | nA μA | $V_{CB} = 136\text{V}$ $V_{CB} = 136\text{V}$, $T_{amb} = 100^{\circ}\text{C}$ |
| Collector emitter cut-off current | I_{CEX} | | - | 100 | nA | $V_{CE} = 136\text{V}$; $R_{BE} < 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$ |
| Emitter cut-off current | I_{EBO} | | <1 | 50 | nA | $V_{EB} = 5.6\text{V}$ |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | | 40 100 70 200 | 55 135 80 250 | mV mV mV mV | $I_C = 0.5\text{A}$, $I_B = 50\text{mA}^{(*)}$ $I_C = 0.5\text{A}$, $I_B = 10\text{mA}^{(*)}$ $I_C = 1\text{A}$, $I_B = 100\text{mA}^{(*)}$ $I_C = 3\text{A}$, $I_B = 300\text{mA}^{(*)}$ |
| Base-emitter saturation voltage | $V_{BE(sat)}$ | | 940 | 1050 | mV | $I_C = 3\text{A}$, $I_B = 300\text{mA}^{(*)}$ |
| Base-emitter turn-on voltage | $V_{BE(on)}$ | | 890 | 1000 | mV | $I_C = 3\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ |
| Static forward current transfer ratio | h_{FE} | 100 50 | 200 85 20 | 300 | | $I_C = 10\text{mA}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 1\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 3\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ |
| Transition frequency | f_T | | 160 | | MHz | $I_C = 100\text{mA}$, $V_{CE} = 5\text{V}$ $f = 100\text{MHz}$ |
| Output capacitance | C_{OBO} | | 9.4 | 20 | pF | $V_{CB} = 10\text{V}$, $f = 1\text{MHz}^{(*)}$ |
| Delay time | $t_{(d)}$ | | 16 | | ns | $V_{CC} = 10\text{V}$, $I_C = 500\text{mA}$, |
| Rise time | $t_{(r)}$ | | 55 | | ns | $I_{B1} = I_{B2} = 50\text{mA}$. |
| Storage time | $t_{(s)}$ | | 677 | | ns | |
| Fall time | $t_{(f)}$ | | 95 | | ns | |

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

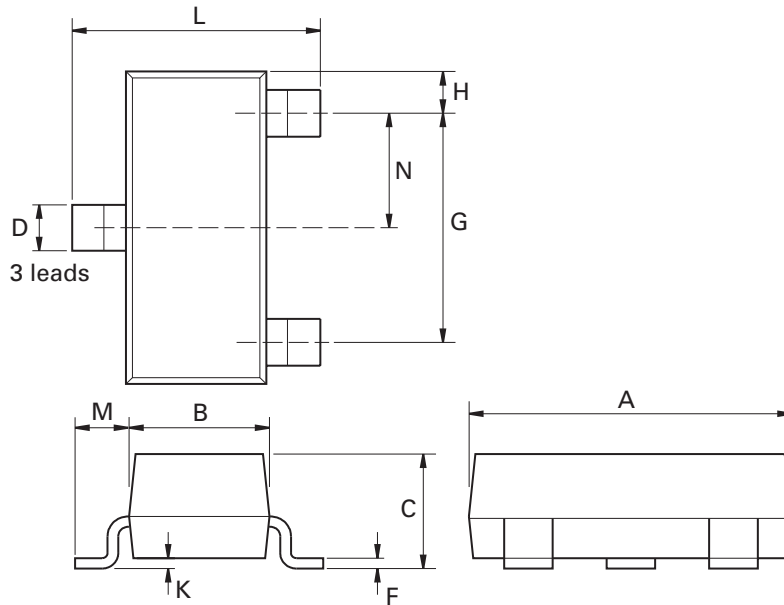
ZXTN25100BFH

Typical characteristics



ZXTN25100BFH

Package outline - SOT23



| Dim. | Millimeters | | Inches | | Dim. | Millimeters | | Inches | |
|------|-------------|------|-----------|--------|------|-------------|------|------------|--------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Max. | Max. |
| A | 2.67 | 3.05 | 0.105 | 0.120 | H | 0.33 | 0.51 | 0.013 | 0.020 |
| B | 1.20 | 1.40 | 0.047 | 0.055 | K | 0.01 | 0.10 | 0.0004 | 0.004 |
| C | - | 1.10 | - | 0.043 | L | 2.10 | 2.50 | 0.083 | 0.0985 |
| D | 0.37 | 0.53 | 0.015 | 0.021 | M | 0.45 | 0.64 | 0.018 | 0.025 |
| F | 0.085 | 0.15 | 0.0034 | 0.0059 | N | 0.95 NOM | | 0.0375 NOM | |
| G | 1.90 NOM | | 0.075 NOM | | - | - | - | - | - |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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